GaN PROTOTYPE ACCELERATOR

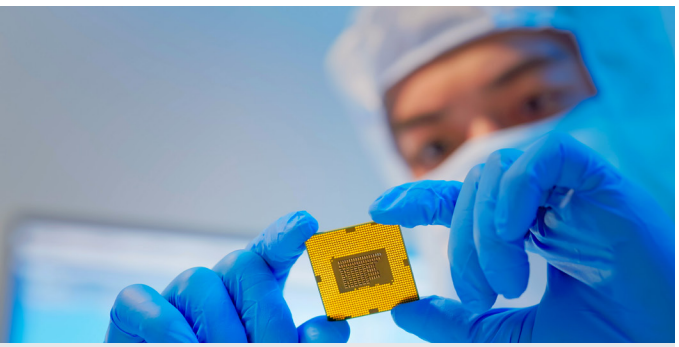
MULTI-PROJECT WAFER OPPORTUNITY

ACCELERATING INNOVATION IN GALLIUM NITRIDE RF POWER DESIGN

MMEC™
ACCELERATE : COLLABORATE : EXECUTE

DREAMS
Defense Ready Electronics and Microdevices Superhub

NORTHROP GRUMMAN



Are You Ready to Shape the Future of GaN?

The GaN Prototype Accelerator is a bold new Multi-Project Wafer (MPW) opportunity designed to fast-track innovation across the domestic GaN ecosystem. Whether you're an established RF designer or a non-traditional innovator, this is your opportunity to see your ideas emerge in a rapid GaN prototype.

WHY PARTICIPATE?

This unique opportunity provides:

- MOSIS 2.0 access to Northrop Grumman Microelectronic Center GaN15 PDK
- 16–25 mm² of MPW die area
- Design support services through CA DREAMS
- EDA tool and cloud compute resources through MMEC DESIGN
- Mission-focused design challenge with national security relevance

PROGRAM OBJECTIVES

- Lower the barrier to entry for advanced GaN technologies
- Foster domestic design and fabrication capabilities
- Enable repeatable and rigorous RF design practices
- Attract diverse and non-traditional design teams
- Strengthen secure, domestic microelectronics solutions

SELECTION CRITERIA

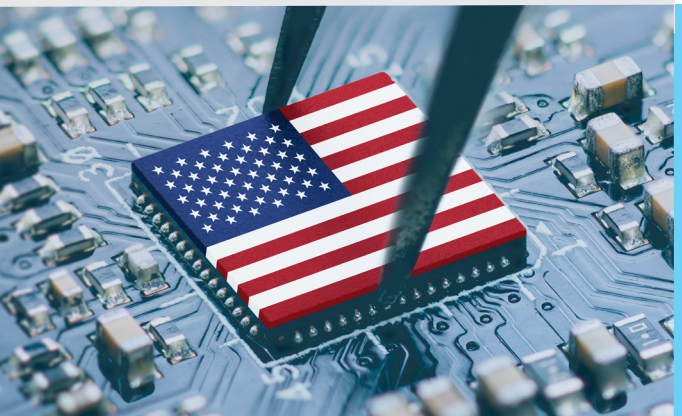
Submissions will be evaluated on:

- Technical merit & innovation
- Application relevance & impact
- Performance objectives
- Team experience and RF design capability
- Potential for technology transition
- Risk mitigation strategies

GET INVOLVED:

www.GaNChallenge.com

info@GaNChallenge.com



"The GaN Prototype Accelerator is more than a design challenge - it's a mission to transform domestic microelectronics by connecting visionaries to real-world impact.